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October 2013

FCB20N60F

N-Channel SuperFET® FRFET® MOSFET

600 V, 20 A, 190 mΩ

Features

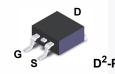
- 650 V @T_{.1} = 150 °C
- Typ. $R_{DS(on)}$ = 150 m Ω
- Ultra Low Gate Charge (Typ. Q_q = 75 nC)
- Low Effective Output Capacitance (Typ. C_{oss}.eff = 165 pF)
- 100% Avalanche Tested
- · RoHS Compliant

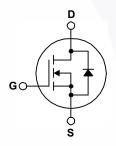
Applications

- Lighting
- · AC-DC Power Supply
- · Solar Inverter

Description

SuperFET® MOSFET is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low onresistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications. SuperFET FRFET® MOSFET's optimized body diode reverse recovery performance can remove additional component and improve system reliability.





MOSFET Maximum Ratings T_C = 25°C unless otherwis noted

Symbol	Parameter		FCB20N60FTM	Unit
V _{DSS}	Drain to Source Voltage		600	V
	Drain Current	- Continuous (T _C = 25°C)	20	_
I _D	Drain Current	- Continuous (T _C = 100°C)	12.5	Α
I _{DM}	Drain Current	- Pulsed (Note 1)	60	Α
V _{GSS}	Gate to Source Voltage		±30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		690	mJ
I _{AR}	Avalanche Current (Note 1)		20	Α
E _{AR}	Repetitive Avalanche Energy (Note		20.8	mJ
dv/dt	Peak Diode Recovery dv/	'dt (Note 3)	50	V/ns
D	Power Dissipation	(T _C = 25°C)	208	W
P_{D}	Power Dissipation	- Derate above 25°C	1.67	W/oC
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	οС
T _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FCB20N60FTM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.6	
D	Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max.	62.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (1 in ² pad of 2 oz copper), Max.	40	·

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FCB20N60F	FCB20N60FTM	D ² -PAK	330mm	24m	800

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS} Drain to Source Breakdown Voltage	Drain to Source Breakdown Voltage	$V_{GS} = 0 \text{ V,I}_{D} = 250 \mu\text{A, T}_{C} = 25^{\circ}\text{C}$	600	-	-	V
	Drain to Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}, T_C = 150^{\circ}\text{C}$	-	650	-	V
ΔBV _{DSS} / ΔΤ _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	-	0.6	-	V/°C
BV _{DS}	Drain-Source Avalanche Breakdown Voltage	V _{GS} = 0 V, I _D = 20 A	-	700	-	V
	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V	-	-	1	
IDSS	Zeio Gate voltage Dialli Cullent	$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	10	μА
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	3.0	-	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	-	0.15	0.19	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 40 \text{ V}, I_{D} = 10 \text{ A}$	-	17	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 05.V V 0.V	- \	2370	3080	pF
C _{oss}	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}$ f = 1.0 MHz	- \	1280	1665	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1.0 WH 12		95	-	pF
C _{oss}	Output Capacitance	V_{DS} = 480 V, V_{GS} = 0 V, f = 1.0 MHz	-	65	85	pF
C _{oss} eff.	Effective Output Capacitance	V _{DS} = 0 V to 400 V, V _{GS} = 0 V	-	165	-	pF

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	62	135	ns
t _r	Turn-On Rise Time	$V_{DD} = 300 \text{ V}, I_{D} = 20 \text{ A}$ $R_{G} = 25 \Omega$		140	290	ns
t _{d(off)}	Turn-Off Delay Time			230	470	ns
t _f	Turn-Off Fall Time	(Note 4	-	65	140	ns
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 480 V, I _D = 20 A,	/-	75	98	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	13.5	18	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note 4	_	36	-	nC

Drain-Source Diode Characteristics

Is	Maximum Continuous Drain to Source Diode Forward Current		-	-	20	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current			-	60	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 20 A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 20 A	-	160	/// -	ns
Q _{rr}	Reverse Recovery Charge	$V_{GS} = 0 \text{ V, } I_{SD} = 20 \text{ A}$ $dI_F/dt = 100 \text{ A/}\mu\text{s}$	-	1.1	-	μС

Notes

- ${\bf 1.}\ {\bf Repetitive}\ {\bf Rating:}\ {\bf Pulse}\ {\bf width}\ {\bf limited}\ {\bf by}\ {\bf maximum}\ {\bf junction}\ {\bf temperature}$
- 2. I_{AS} = 10 A, V_{DD} = 50 V, R_{G} = 25 Ω , Starting T_{J} = 25°C
- 3. I $_{SD} \le 20$ A, di/dt ≤ 1200 A/µs, V $_{DD} \le BV _{DSS},$ Starting T $_{J}$ = 25°C
- 4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

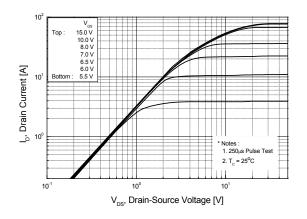


Figure 2. Transfer Characteristics

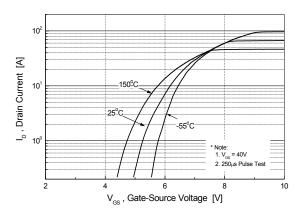


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

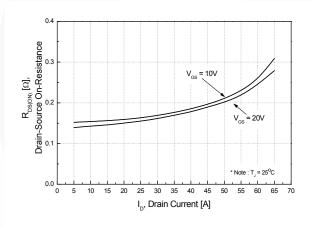


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

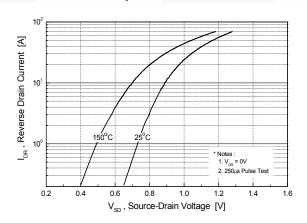


Figure 5. Capacitance Characteristics

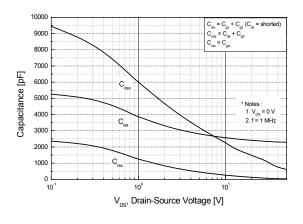
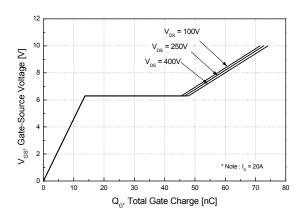


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

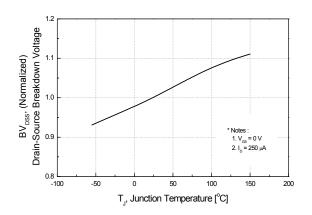


Figure 8. On-Resistance Variation vs. Temperature

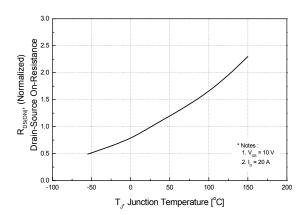


Figure 9. Maximum Safe Operating Area

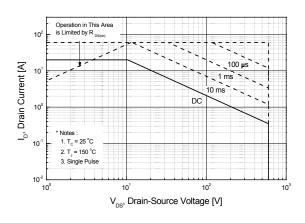


Figure 10. Maximum Drain Current vs. Case Temperature

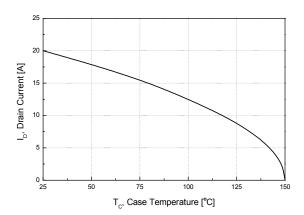


Figure 11. Transient Thermal Response Curve

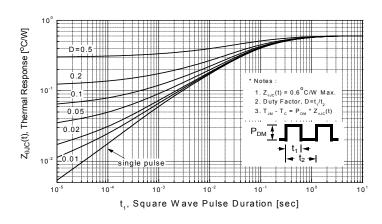


Figure 12. Gate Charge Test Circuit & Waveform

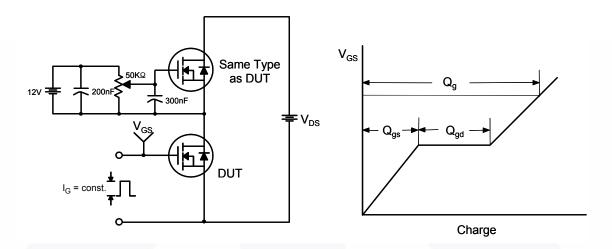


Figure 13. Resistive Switching Test Circuit & Waveforms

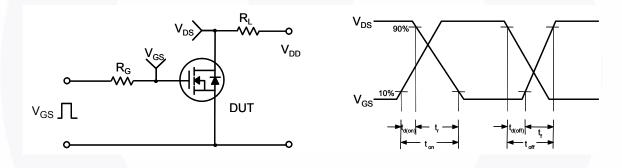
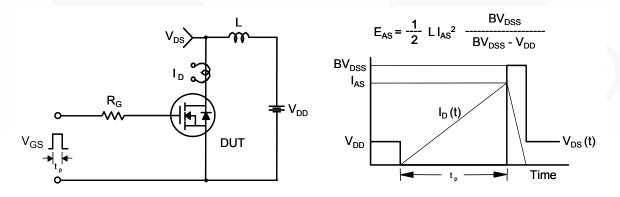


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



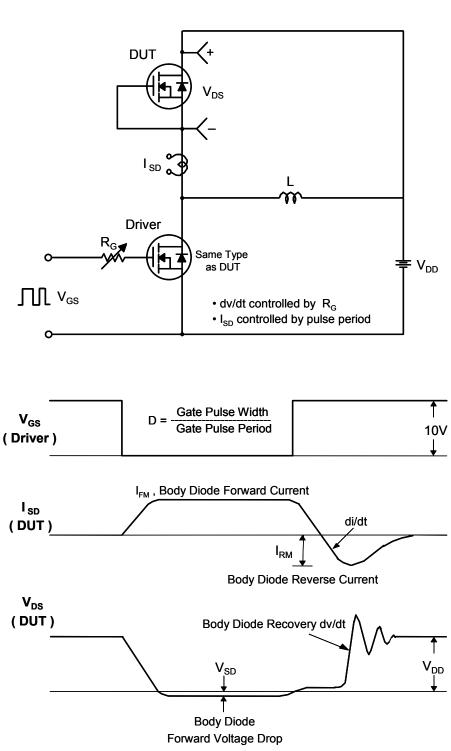


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

TO-263 2L (D²PAK)

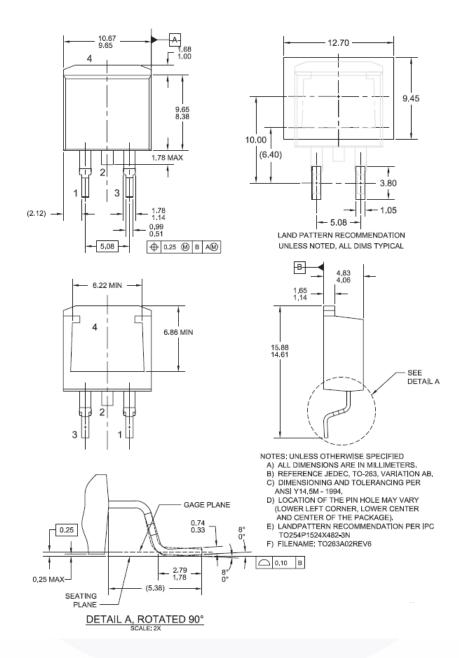


Figure 16. 2LD, TO263, Surface Mount

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Dimension in Millimeters





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